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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (3)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	620-BBGA Exposed Pad
Supplier Device Package	620-PBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8343eczqagdb

  - Up to four physical banks (chip selects), each bank up to 1 Gbyte independently addressable
  - DRAM chip configurations from 64 Mbits to 1 Gbit with ×8/×16 data ports
  - Full error checking and correction (ECC) support
  - Support for up to 16 simultaneous open pages (up to 32 pages for DDR2)
  - Contiguous or discontiguous memory mapping
  - Read-modify-write support
  - Sleep-mode support for SDRAM self refresh
  - Auto refresh
  - On-the-fly power management using CKE
  - Registered DIMM support
  - 2.5-V SSTL2 compatible I/O for DDR1, 1.8-V SSTL2 compatible I/O for DDR2
- Dual three-speed (10/100/1000) Ethernet controllers (TSECs)
  - Dual controllers designed to comply with IEEE 802.3™, 802.3u™, 820.3x™, 802.3z™, 802.3ac™ standards
  - Ethernet physical interfaces:
    - 1000 Mbps IEEE Std. 802.3 RGMII, IEEE Std. 802.3z RTBI, full-duplex
    - 10/100 Mbps IEEE Std. 802.3 MII full- and half-duplex
  - Buffer descriptors are backward-compatible with MPC8260 and MPC860T 10/100 programming models
  - 9.6-Kbyte jumbo frame support
  - RMON statistics support
  - Internal 2-Kbyte transmit and 2-Kbyte receive FIFOs per TSEC module
  - MII management interface for control and status
  - Programmable CRC generation and checking
- PCI interface
  - Designed to comply with *PCI Specification Revision 2.3*
  - Data bus width:
    - 32-bit data PCI interface operating at up to 66 MHz
  - PCI 3.3-V compatible
  - PCI host bridge capabilities
  - PCI agent mode on PCI interface
  - PCI-to-memory and memory-to-PCI streaming
  - Memory prefetching of PCI read accesses and support for delayed read transactions
  - Posting of processor-to-PCI and PCI-to-memory writes
  - On-chip arbitration supporting five masters on PCI
  - Accesses to all PCI address spaces
  - Parity supported
  - Selectable hardware-enforced coherency

- Address translation units for address mapping between host and peripheral
- Dual address cycle for target
- Internal configuration registers accessible from PCI

- Security engine is optimized to handle all the algorithms associated with IPSec, SSL/TLS, SRTP, IEEE Std. 802.11i®, iSCSI, and IKE processing. The security engine contains four crypto-channels, a controller, and a set of crypto execution units (EUs):
  - Public key execution unit (PKEU) :
    - RSA and Diffie-Hellman algorithms
    - Programmable field size up to 2048 bits
    - Elliptic curve cryptography
    - F2m and F(p) modes
    - Programmable field size up to 511 bits
  - Data encryption standard (DES) execution unit (DEU)
    - DES and 3DES algorithms
    - Two key (K1, K2) or three key (K1, K2, K3) for 3DES
    - ECB and CBC modes for both DES and 3DES
  - Advanced encryption standard unit (AESU)
    - Implements the Rijndael symmetric-key cipher
    - Key lengths of 128, 192, and 256 bits
    - ECB, CBC, CCM, and counter (CTR) modes
  - XOR parity generation accelerator for RAID applications
  - ARC four execution unit (AFEU)
    - Stream cipher compatible with the RC4 algorithm
    - 40- to 128-bit programmable key
  - Message digest execution unit (MDEU)
    - SHA with 160-, 224-, or 256-bit message digest
    - MD5 with 128-bit message digest
    - HMAC with either algorithm
  - Random number generator (RNG)
  - Four crypto-channels, each supporting multi-command descriptor chains
    - Static and/or dynamic assignment of crypto-execution units through an integrated controller
    - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
- Universal serial bus (USB) dual role controller
  - USB on-the-go mode with both device and host functionality
  - Complies with USB specification Rev. 2.0
  - Can operate as a stand-alone USB device
    - One upstream facing port
    - Six programmable USB endpoints

Table 1. Absolute Maximum Ratings[1] (continued)

Parameter		Symbol	Max Value	Unit	Notes
Input voltage	DDR DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	DDR DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	Three-speed Ethernet signals	LV_{IN}	–0.3 to (LV_{DD} + 0.3)	V	4, 5
	Local bus, DUART, CLKIN, system control and power management, I^2C, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	3, 5
	PCI	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	6
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:
1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
2. **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
3. **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
4. **Caution:** LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
5. (M,L,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.
6. OVIN on the PCI interface can overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

2.1.2 Power Supply Voltage Specification

Table 2 provides the recommended operating conditions for the MPC8343EA. Note that the values in Table 2 are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Parameter	Symbol	Recommended Value	Unit	Notes
Core supply voltage	V_{DD}	1.2 V ± 60 mV	V	1
PLL supply voltage	AV_{DD}	1.2 V ± 60 mV	V	1
DDR and DDR2 DRAM I/O voltage	GV_{DD}	2.5 V ± 125 mV 1.8 V ± 90 mV	V	—
Three-speed Ethernet I/O supply voltage	LV_{DD1}	3.3 V ± 330 mV 2.5 V ± 125 mV	V	—
Three-speed Ethernet I/O supply voltage	LV_{DD2}	3.3 V ± 330 mV 2.5 V ± 125 mV	V	—

Table 2. Recommended Operating Conditions (continued)

Parameter	Symbol	Recommended Value	Unit	Notes
PCI, local bus, DUART, system control and power management, I^2C, and JTAG I/O voltage	OV_{DD}	3.3 V ± 330 mV	V	—

Note:
1 GV_{DD}, LV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.

Figure 2 shows the undershoot and overshoot voltages at the interfaces of the MPC8343EA.

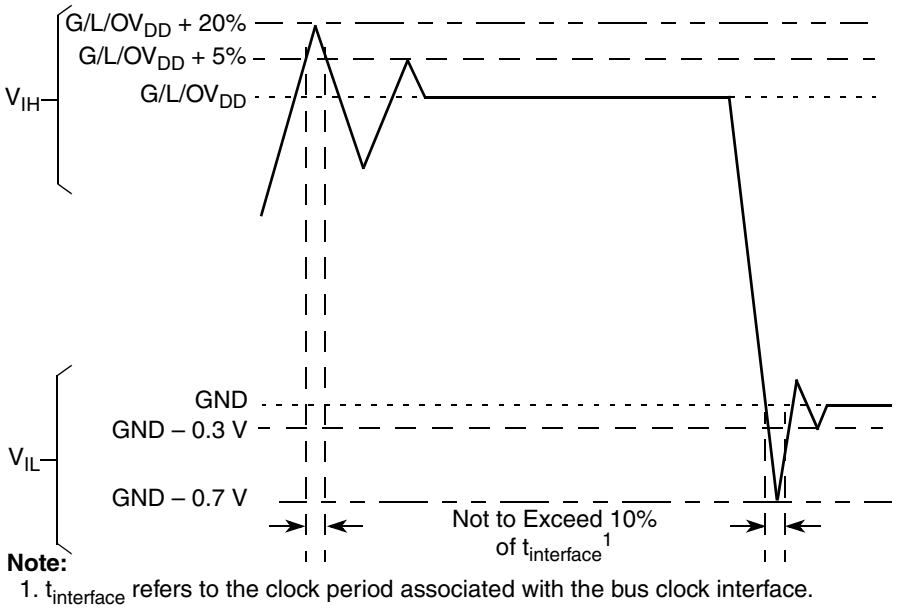


Figure 2. Overshoot/Undershoot Voltage for $GV_{DD}/OV_{DD}/LV_{DD}$

Table 16 provides the current draw characteristics for MV_{REF}.

Table 16. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Note
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:
1. The voltage regulator for MV_{REF} must supply up to 500 μA current.

6.2 DDR and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR and DDR2 SDRAM interface.

6.2.1 DDR and DDR2 SDRAM Input AC Timing Specifications

Table 17 provides the input AC timing specifications for the DDR2 SDRAM when GV_{DD}(typ) = 1.8 V.

Table 17. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with GV_{DD} of 1.8 ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V	—

Table 18 provides the input AC timing specifications for the DDR SDRAM when GV_{DD}(typ) = 2.5 V.

Table 18. DDR SDRAM Input AC Timing Specifications for 2.5-V Interface

At recommended operating conditions with GV_{DD} of 2.5 ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.31	—	V	—

Table 19 provides the input AC timing specifications for the DDR SDRAM interface.

Table 19. DDR and DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC/MDM	t_{CISKEW}			ps	1, 2
400 MHz		–600	600		3
333 MHz		–750	750		—

8.2 MII, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for MII, RGMII, and RTBI are presented in this section.

8.2.1 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.1.1 MII Transmit AC Timing Specifications

Table 25 provides the MII transmit AC timing specifications.

Table 25. MII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise (20%–80%)	t_{MTXR}	1.0	—	4.0	ns
TX_CLK data clock fall (80%–20%)	t_{MTXF}	1.0	—	4.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). In general, the clock reference symbol is based on two to three letters representing the clock of a particular function. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 9 shows the MII transmit AC timing diagram.

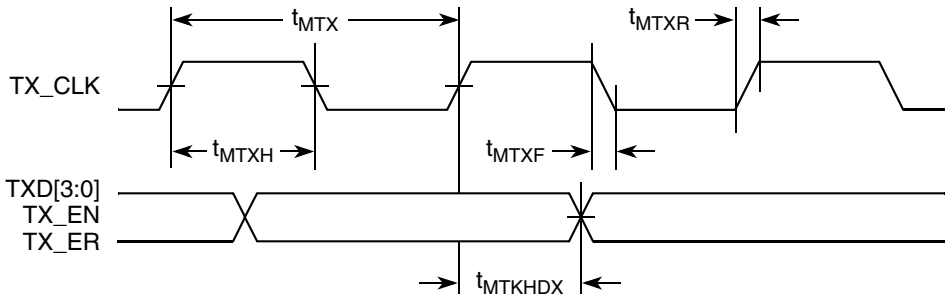


Figure 9. MII Transmit AC Timing Diagram

Figure 17 through Figure 22 show the local bus signals.

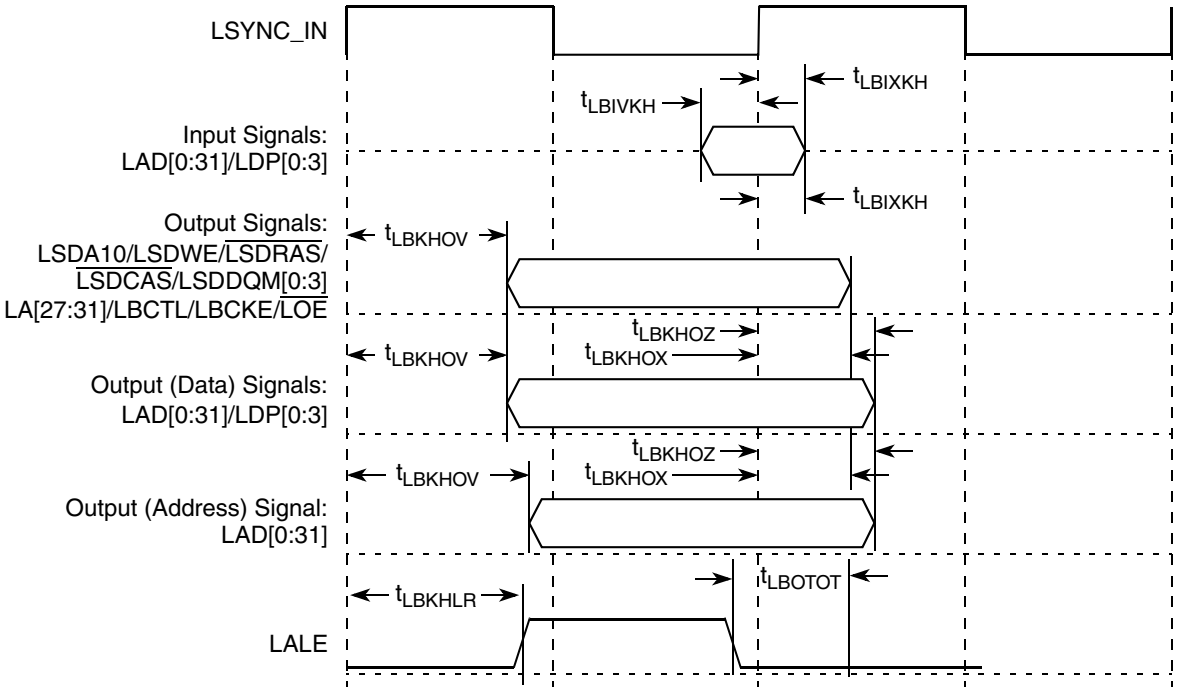


Figure 17. Local Bus Signals, Nonspecial Signals Only (DLL Enabled)

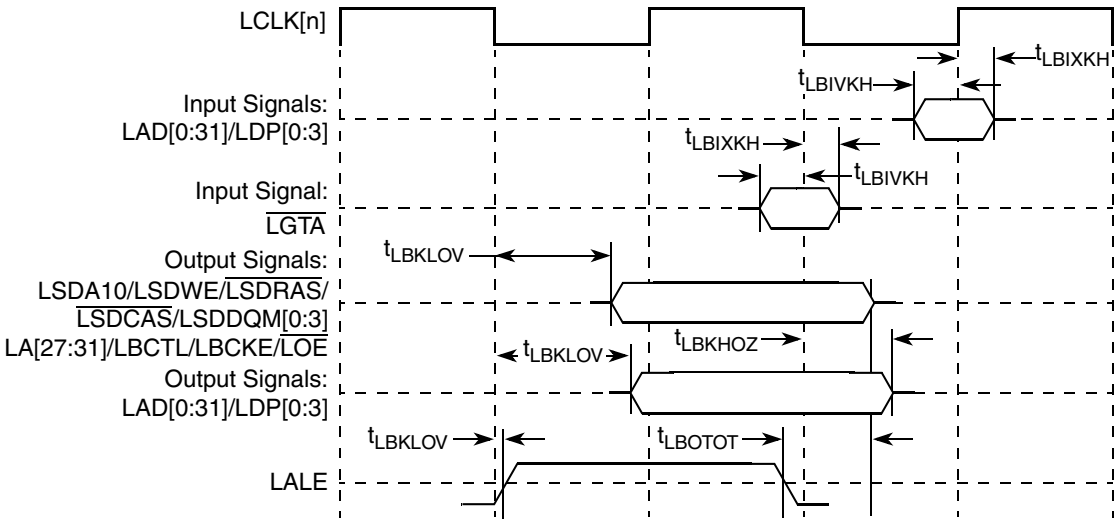


Figure 18. Local Bus Signals, Nonspecial Signals Only (DLL Bypass Mode)

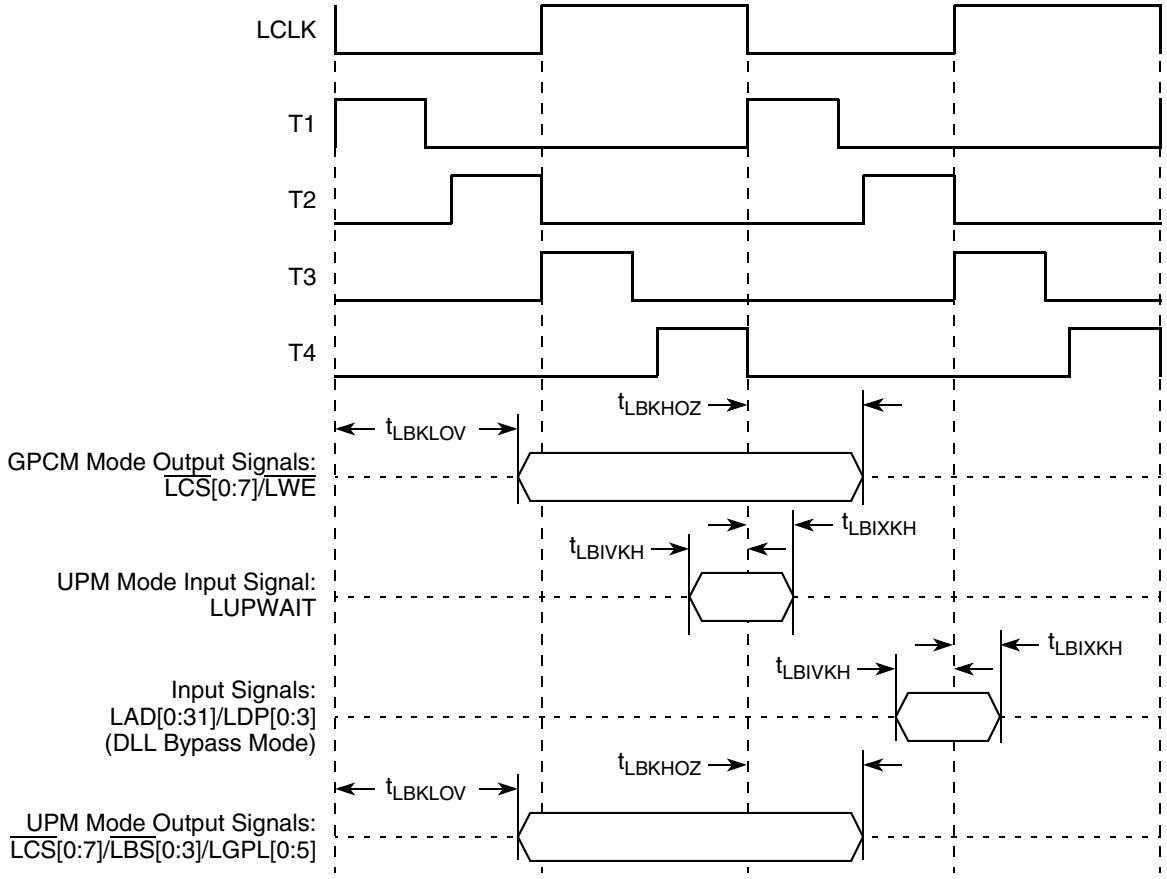


Figure 21. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (DLL Bypass Mode)

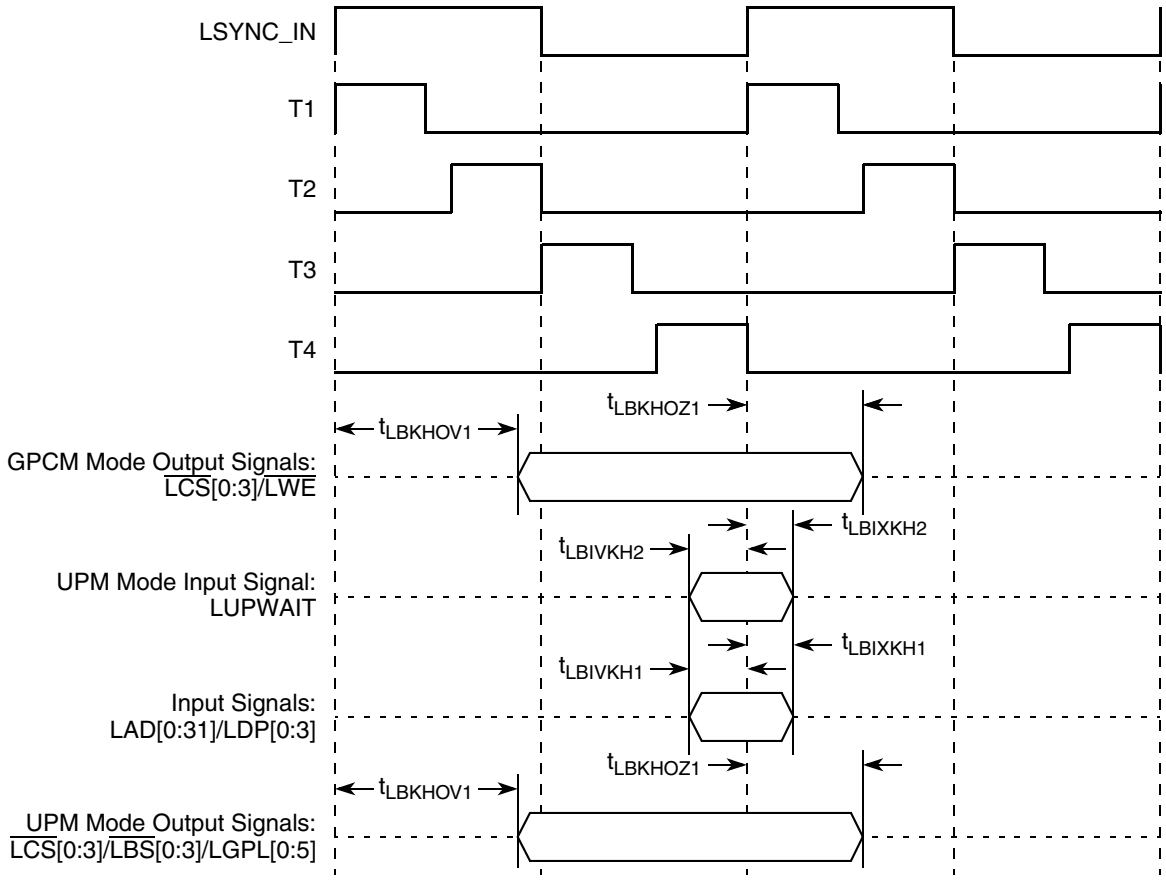


Figure 22. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (DLL Enabled)

11 JTAG

This section describes the DC and AC electrical specifications for the IEEE Std. 1149.1 (JTAG) interface of the MPC8343EA.

11.1 JTAG DC Electrical Characteristics

Table 36 provides the DC electrical characteristics for the IEEE Std. 1149.1 (JTAG) interface of the MPC8343EA.

Table 36. JTAG Interface DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	OV_{DD} – 0.3	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V

12 I²C

This section describes the DC and AC electrical characteristics for the I²C interface of the MPC8343EA.

12.1 I²C DC Electrical Characteristics

Table 38 provides the DC electrical characteristics for the I²C interface of the MPC8343EA.

Table 38. I²C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 10%.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	$0.2 \times OV_{DD}$	V	1
Output fall time from V_{IH}(min) to V_{IL}(max) with a bus capacitance from 10 to 400 pF	t_{I2KLKV}	$20 + 0.1 \times C_B$	250	ns	2
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	3
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max)	I_I	–10	10	μA	4
Capacitance for each I/O pin	C_I	—	10	pF	—

Notes:
1. Output voltage (open drain or open collector) condition = 3 mA sink current.
2. C_B = capacitance of one bus line in pF.
3. Refer to the *MPC8349EA Integrated Host Processor Family Reference Manual,* for information on the digital filter used.
4. I/O pins obstruct the SDA and SCL lines if OV_{DD} is switched off.

12.2 I²C AC Electrical Specifications

Table 39 provides the AC timing parameters for the I²C interface of the MPC8343EA. Note that all values refer to V_{IH}(min) and V_{IL}(max) levels (see Table 38).

Table 39. I²C AC Electrical Specifications

Parameter	Symbol[1]	Min	Max	Unit
SCL clock frequency	f_{I2C}	0	400	kHz
Low period of the SCL clock	t_{I2CL}	1.3	—	μs
High period of the SCL clock	t_{I2CH}	0.6	—	μs
Setup time for a repeated START condition	t_{I2SVKH}	0.6	—	μs
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t_{I2SXKL}	0.6	—	μs
Data setup time	t_{I2DVKH}	100	—	ns
Data hold time:CBUS compatible masters I²C bus devices	t_{I2DXKL}	— 0[2]	— 0.9[3]	μs

Figure 31 shows the PCI input AC timing diagram.

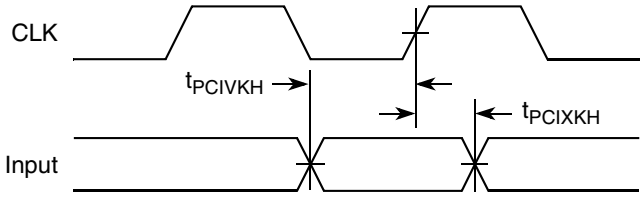


Figure 31. PCI Input AC Timing Diagram

Figure 32 shows the PCI output AC timing diagram.

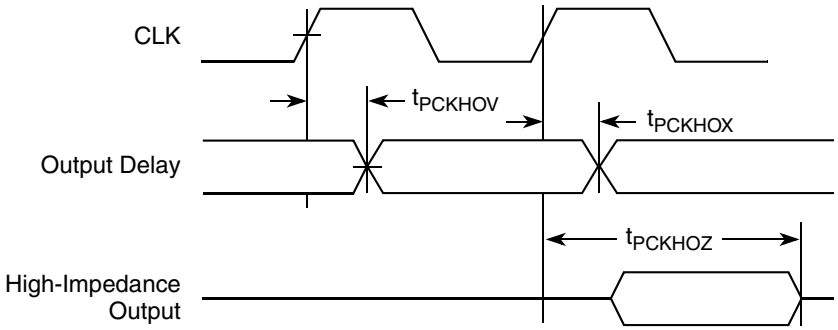


Figure 32. PCI Output AC Timing Diagram

14 Timers

This section describes the DC and AC electrical specifications for the timers.

14.1 Timer DC Electrical Characteristics

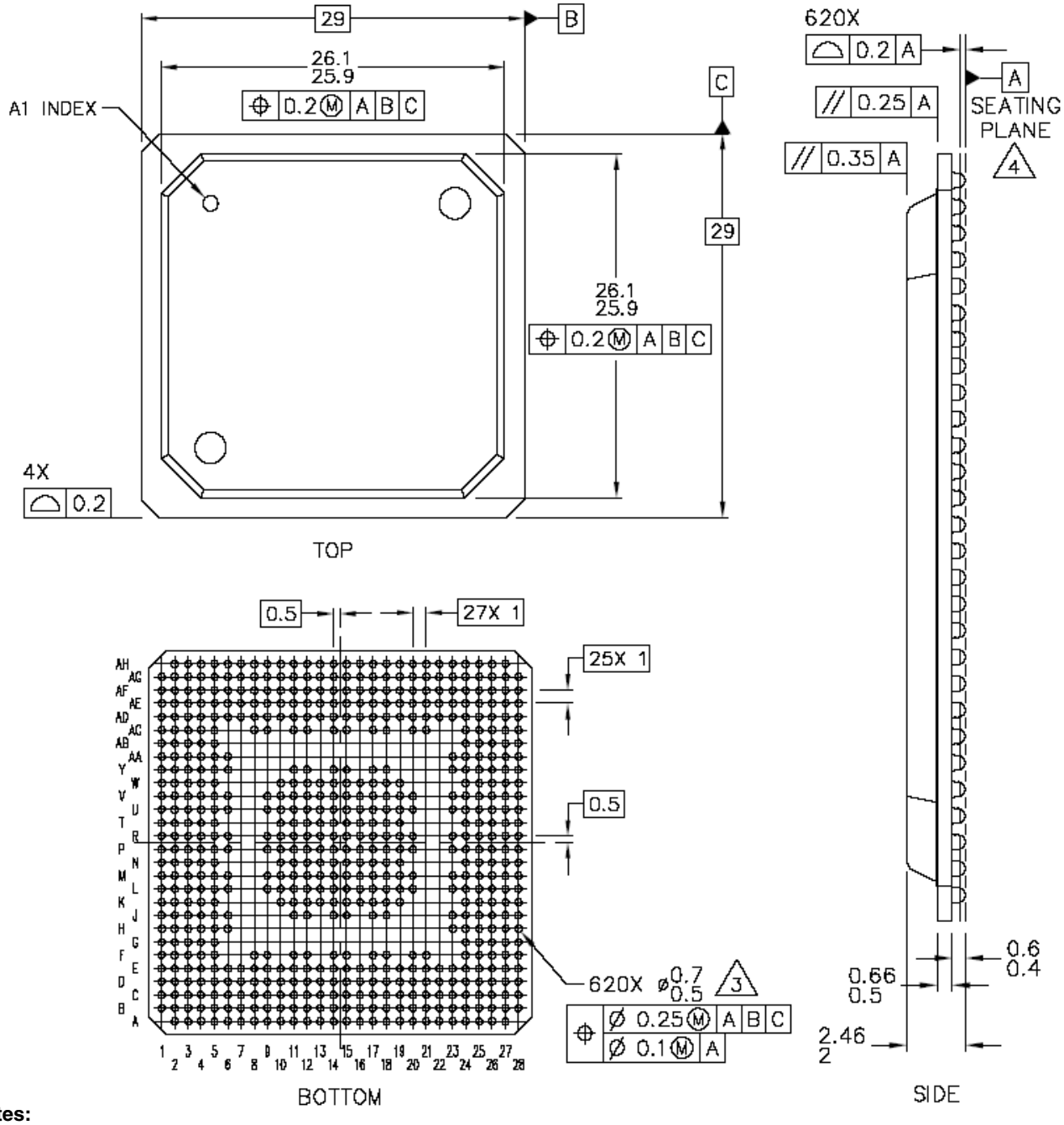
Table 43 provides the DC electrical characteristics for the MPC8343EA timer pins, including TIN, $\overline{\text{TOUT}}$, $\overline{\text{TGATE}}$, and RTC_CLK.

Table 43. Timer DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

18.2 Mechanical Dimensions for the MPC8343EA PBGA

Figure 36 shows the mechanical dimensions and bottom surface nomenclature for the MPC8343EA, 620-PBGA package.



Notes:

1. All dimensions are in millimeters.
2. Dimensioning and tolerancing per ASME Y14. 5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.

Figure 36. Mechanical Dimensions and Bottom Surface Nomenclature for the MPC8343EA PBGA

Table 51. MPC8343EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LBCTL	H5	O	OV_{DD}	—
LALE	E3	O	OV_{DD}	—
LGPL0/LSDA10/cfg_reset_source0	F4	I/O	OV_{DD}	—
LGPL1/$\overline{\text{LSDWE}}$/cfg_reset_source1	D2	I/O	OV_{DD}	—
LGPL2/$\overline{\text{LSDRAS}}$/$\overline{\text{LOE}}$	C1	O	OV_{DD}	—
LGPL3/$\overline{\text{LSDCAS}}$/cfg_reset_source2	C2	I/O	OV_{DD}	—
LGPL4/$\overline{\text{LGTA}}$/LUPWAIT/LPBSE	C3	I/O	OV_{DD}	12
LGPL5/cfg_clkin_div	B3	I/O	OV_{DD}	—
LCKE	E4	O	OV_{DD}	—
LCLK[0:2]	D4, A3, C4	O	OV_{DD}	—
LSYNC_OUT	U3	O	OV_{DD}	—
LSYNC_IN	Y2	I	OV_{DD}	—
General Purpose I/O Timers				
GPIO1[0]/$\overline{\text{DMA\_DREQ0}}$/GTM1_TIN1/ GTM2_TIN2	D27	I/O	OV_{DD}	—
GPIO1[1]/$\overline{\text{DMA\_DACK0}}$/$\overline{\text{GTM1\_TGATE1}}$/ $\overline{\text{GTM2\_TGATE2}}$	E26	I/O	OV_{DD}	—
GPIO1[2]/$\overline{\text{DMA\_DDONE0}}$/ $\overline{\text{GTM1\_TOUT1}}$	D28	I/O	OV_{DD}	—
GPIO1[3]/$\overline{\text{DMA\_DREQ1}}$/GTM1_TIN2/ GTM2_TIN1	G25	I/O	OV_{DD}	—
GPIO1[4]/$\overline{\text{DMA\_DACK1}}$/ $\overline{\text{GTM1\_TGATE2}}$/$\overline{\text{GTM2\_TGATE1}}$	J24	I/O	OV_{DD}	—
GPIO1[5]/$\overline{\text{DMA\_DDONE1}}$/ $\overline{\text{GTM1\_TOUT2}}$/$\overline{\text{GTM2\_TOUT1}}$	F26	I/O	OV_{DD}	—
GPIO1[6]/$\overline{\text{DMA\_DREQ2}}$/GTM1_TIN3/ GTM2_TIN4	E27	I/O	OV_{DD}	—
GPIO1[7]/$\overline{\text{DMA\_DACK2}}$/$\overline{\text{GTM1\_TGATE3}}$/ $\overline{\text{GTM2\_TGATE4}}$	E28	I/O	OV_{DD}	—
GPIO1[8]/$\overline{\text{DMA\_DDONE2}}$/ $\overline{\text{GTM1\_TOUT3}}$	H25	I/O	OV_{DD}	—
GPIO1[9]/$\overline{\text{DMA\_DREQ3}}$/GTM1_TIN4/ GTM2_TIN3	F27	I/O	OV_{DD}	—
GPIO1[10]/$\overline{\text{DMA\_DACK3}}$/ $\overline{\text{GTM1\_TGATE4}}$/$\overline{\text{GTM2\_TGATE3}}$	K24	I/O	OV_{DD}	—
GPIO1[11]/$\overline{\text{DMA\_DDONE3}}$/ $\overline{\text{GTM1\_TOUT4}}$/$\overline{\text{GTM2\_TOUT3}}$	G26	I/O	OV_{DD}	—

Table 51. MPC8343EA (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
USB				
DR_D0_ENABLEN	C28	I/O	OV_{DD}	—
DR_D1_SER_TXD	F25	I/O	OV_{DD}	—
DR_D2_VMO_SE0	B28	I/O	OV_{DD}	—
DR_D3_SPEED	C27	I/O	OV_{DD}	—
DR_D4_DP	D26	I/O	OV_{DD}	—
DR_D5_DM	E25	I/O	OV_{DD}	—
DR_D6_SER_RCV	C26	I/O	OV_{DD}	—
DR_D7_DRVVBUS	D25	I/O	OV_{DD}	—
DR_SESS_VLD_NXT	B26	I	OV_{DD}	—
DR_XCVR_SEL_DPPULLUP	E24	I/O	OV_{DD}	—
DR_STP_SUSPEND	A27	O	OV_{DD}	—
DR_RX_ERROR_PWRFAULT	C25	I	OV_{DD}	—
DR_TX_VALID_PCTL0	A26	O	OV_{DD}	—
DR_TX_VALIDH_PCTL1	B25	O	OV_{DD}	—
DR_CLK	A25	I	OV_{DD}	—
Programmable Interrupt Controller				
$\overline{\text{MCP\_OUT}}$	E8	O	OV_{DD}	2
$\overline{\text{IRQ}}$0/$\overline{\text{MCP_IN}}$/GPIO2[12]	J28	I/O	OV_{DD}	—
$\overline{\text{IRQ}}$[1:5]/GPIO2[13:17]	K25, J25, H26, L24, G27	I/O	OV_{DD}	—
$\overline{\text{IRQ}}$[6]/GPIO2[18]/CKSTOP_OUT	G28	I/O	OV_{DD}	—
$\overline{\text{IRQ}}$[7]/GPIO2[19]/CKSTOP_IN	J26	I/O	OV_{DD}	—
Ethernet Management Interface				
EC_MDC	Y24	O	LV_{DD1}	—
EC_MDIO	Y25	I/O	LV_{DD1}	11
Gigabit Reference Clock				
EC_GTX_CLK125	Y26	I	LV_{DD1}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 1)				
TSEC1_COL/GPIO2[20]	M26	I/O	OV_{DD}	—
TSEC1_CRS/GPIO2[21]	U25	I/O	LV_{DD1}	—
TSEC1_GTX_CLK	V24	O	LV_{DD1}	3
TSEC1_RX_CLK	U26	I	LV_{DD1}	—

As shown in Figure 37, the primary clock input (frequency) is multiplied up by the system phase-locked loop (PLL) and the clock unit to create the coherent system bus clock (*csb_clk*), the internal clock for the DDR controller (*ddr_clk*), and the internal clock for the local bus interface unit (*lbiu_clk*).

The *csb_clk* frequency is derived from a complex set of factors that can be simplified into the following equation:

$$csb\_clk = \{PCI\_SYNC\_IN \times (1 + CFG\_CLKIN\_DIV)\} \times SPMF$$

In PCI host mode, PCI_SYNC_IN × (1 + CFG_CLKIN_DIV) is the CLKIN frequency.

The *csb_clk* serves as the clock input to the e300 core. A second PLL inside the e300 core multiplies the *csb_clk* frequency to create the internal clock for the e300 core (*core_clk*). The system and core PLL multipliers are selected by the SPMF and COREPLL fields in the reset configuration word low (RCWL), which is loaded at power-on reset or by one of the hard-coded reset options. See the chapter on reset, clocking, and initialization in the *MPC8349EA Reference Manual* for more information on the clock subsystem.

The internal *ddr_clk* frequency is determined by the following equation:

$$ddr\_clk = csb\_clk \times (1 + RCWL[DDRCM])$$

ddr_clk is not the external memory bus frequency; *ddr_clk* passes through the DDR clock divider (÷2) to create the differential DDR memory bus clock outputs (MCK and $\overline{\text{MCK}}$). However, the data rate is the same frequency as *ddr_clk*.

The internal *lbiu_clk* frequency is determined by the following equation:

$$lbiu\_clk = csb\_clk \times (1 + RCWL[LBIUCM])$$

lbiu_clk is not the external local bus frequency; *lbiu_clk* passes through the LBIU clock divider to create the external local bus clock outputs (LSYNC_OUT and LCLK[0:2]). The LBIU clock divider ratio is controlled by LCCR[CLKDIV].

In addition, some of the internal units may have to be shut off or operate at lower frequency than the *csb_clk* frequency. Those units have a default clock ratio that can be configured by a memory-mapped register after the device exits reset. Table 52 specifies which units have a configurable clock frequency.

Table 52. Configurable Clock Units

Unit	Default Frequency	Options
TSEC1	*csb_clk/3*	Off, *csb_clk, csb_clk/2, csb_clk/3*
TSEC2, I^2C1	*csb_clk/3*	Off, *csb_clk, csb_clk/2, csb_clk/3*
Security core	*csb_clk/3*	Off, *csb_clk,* csb_clk/2, *csb_clk/3*
USB DR, USB MPH	*csb_clk/3*	Off, csb_clk, csb_clk/2, *csb_clk/3*
PCI and DMA complex	*csb_clk*	Off, *csb_clk*

All frequency combinations shown in the table below may not be available. Maximum operating frequencies depend on the part ordered, see Section 22.1, “Part Numbers Fully Addressed by This Document,” for part ordering details and contact your Freescale Sales Representative or authorized distributor for more information.

Table 56. CSB Frequency Options for Agent Mode (continued)

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk* : Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
High	0011	6 : 1	100	150	200	
High	0100	8 : 1	133	200	266	
High	0101	10 : 1	166	250	333	
High	0110	12 : 1	200	300		
High	0111	14 : 1	233			
High	1000	16 : 1	266			

1 CFG_CLKIN_DIV doubles csb_clk if set high.

2 CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

DDR2 memory may be used at 133 MHz provided that the memory components are specified for operation at this frequency.

19.2 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). Table 57 shows the encodings for RCWL[COREPLL]. COREPLL values that are not listed in Table 57 should be considered as reserved.

NOTE

Core VCO frequency = core frequency × VCO divider

VCO divider must be set properly so that the core VCO frequency is in the range of 800–1800 MHz.

Table 57. e300 Core PLL Configuration

RCWL[COREPLL]			*core_clk* : *csb_clk* Ratio	VCO Divider[1]
0–1	2–5	6		
nn	**0000**	n	PLL bypassed (PLL off, *csb_clk* clocks core directly)	PLL bypassed (PLL off, *csb_clk* clocks core directly)
00	**0001**	0	1:1	2
01	**0001**	0	1:1	4
10	**0001**	0	1:1	8
11	**0001**	0	1:1	8
00	**0001**	1	1.5:1	2
01	**0001**	1	1.5:1	4
10	**0001**	1	1.5:1	8
11	**0001**	1	1.5:1	8

The junction-to-ambient thermal resistance is an industry-standard value that provides a quick and easy estimation of thermal performance. Generally, the value obtained on a single-layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J - T_A$) are possible.

20.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)

T_A = ambient temperature for the package (°C)

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

20.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, use the thermal characterization parameter (Ψ_{JT}) to determine the junction temperature and a measure of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

T_J = junction temperature (°C)

T_T = thermocouple temperature on top of package (°C)

Ψ_{JT} = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per the JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so

that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

20.2.4 Heat Sinks and Junction-to-Case Thermal Resistance

Some application environments require a heat sink to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

where:

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)
$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)
$R_{\theta CA}$ = case-to-ambient thermal resistance (°C/W)

$R_{\theta JC}$ is device-related and cannot be influenced by the user. The user controls the thermal environment to change the case-to-ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed-circuit board, or change the thermal dissipation on the printed-circuit board surrounding the device.

The thermal performance of devices with heat sinks has been simulated with a few commercially available heat sinks. The heat sink choice is determined by the application environment (temperature, air flow, adjacent component power dissipation) and the physical space available. Because there is not a standard application environment, a standard heat sink is not required.

Table 60 shows heat sink thermal resistance for PBGA of the MPC8343EA.

Table 60. Heat Sink and Thermal Resistance of MPC8343EA (PBGA)

Heat Sink Assuming Thermal Grease	Air Flow	29 × 29 mm PBGA
		Thermal Resistance
AAVID 30 × 30 × 9.4 mm pin fin	Natural convection	13.5
AAVID 30 × 30 × 9.4 mm pin fin	1 m/s	9.6
AAVID 30 × 30 × 9.4 mm pin fin	2 m/s	8.8
AAVID 31 × 35 × 23 mm pin fin	Natural convection	11.3
AAVID 31 × 35 × 23 mm pin fin	1 m/s	8.1
AAVID 31 × 35 × 23 mm pin fin	2 m/s	7.5
Wakefield, 53 × 53 × 25 mm pin fin	Natural convection	9.1
Wakefield, 53 × 53 × 25 mm pin fin	1 m/s	7.1
Wakefield, 53 × 53 × 25 mm pin fin	2 m/s	6.5
MEI, 75 × 85 × 12 no adjacent board, extrusion	Natural convection	10.1

$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)
P_D = power dissipation (W)

21 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8343EA.

21.1 System Clocking

The MPC8343EA includes two PLLs:

1. The platform PLL generates the platform clock from the externally supplied CLKIN input. The frequency ratio between the platform and CLKIN is selected using the platform PLL ratio configuration bits as described in Section 19.1, “System PLL Configuration.”
2. The e300 core PLL generates the core clock as a slave to the platform clock. The frequency ratio between the e300 core clock and the platform clock is selected using the e300 PLL ratio configuration bits as described in Section 19.2, “Core PLL Configuration.”

21.2 PLL Power Supply Filtering

Each PLL gets power through independent power supply pins ($AV_{DD}1$, $AV_{DD}2$, respectively). The AV_{DD} level should always equal to V_{DD}, and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme.

There are a number of ways to provide power reliably to the PLLs, but the recommended solution is to provide four independent filter circuits as illustrated in Figure 38, one to each of the four AV_{DD} pins. Independent filters to each PLL reduce the opportunity to cause noise injection from one PLL to the other.

The circuit filters noise in the PLL resonant frequency range from 500 kHz to 10 MHz. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

To minimize noise coupled from nearby circuits, each circuit should be placed as closely as possible to the specific AV_{DD} pin being supplied. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of package, without the inductance of vias.

Figure 38 shows the PLL power supply filter circuit.

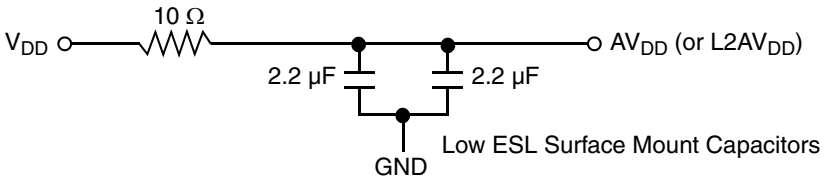


Figure 38. PLL Power Supply Filter Circuit

23 Document Revision History

This table provides a revision history of this document.

Table 64. Document Revision History

Rev. Number	Date	Substantive Change(s)
11	09/2011	• In Section 2.2, "Power Sequencing," added Section 2.2.1, "Power-Up Sequencing" and Figure 4. • In Table 25, Table 29, and Table 27, removed the GTX_CLK125. • In Table 30, updated t_{MDKHDX} Max value from 170ns to 70ns.
10	11/2010	• In Table 51, added overbar to $\overline{LCS}$[4] and $\overline{LCS}$[5] signals. In Table 51 added note for pin LGPL4. • In Section 21.7, "Pull-Up Resistor Requirements, updated the list of open drain type pins.
9	05/2010	• In Table 25 through Table 26, changed V_{IL}(min) to V_{IH}(max) to (20%–80%). • Added Table 8, "EC_GTX_CLK125 AC Timing Specifications."
8	5/2009	• In Section 18.1, "Package Parameters for the MPC8343EA PBGA, changed solder ball for TBGA and PBGA from 95.5 Sn/0.5 Cu/4 Ag to 96.5 Sn/3.5 Ag. • In Table 53, added two columns for the DDR1 and DDR2 memory bus frequency. • In Table 62, footnote 1, changed 667(TBGA) to 533(TBGA). footnote 4, added data rate for DDR1 and DDR2.
7	2/2009	• Added footnote 6 to Table 7. • In Section 9.2, "USB AC Electrical Specifications," clarified that AC table is for ULPI only. • In Table 35, corrected t_{LBKHOV} parameter to t_{LBKLOV} (output data is driven on falling edge of clock in DLL bypass mode). Similarly, made the same correction to Figure 18, Figure 20, and Figure 21 for output signals. • Added footnote 10 to Table 51. • In Table 51, updated note 11 to say the following: "SEC1_TXD[3] is required an external pull-up resistor. For proper functionality of the device, this pin must be pulled up or actively driven high during a hard reset. No external pull-down resistors are allowed to be attached to this net." • In Section 21.1, "System Clocking," removed "(AVDD1)" and "(AVDD2") from bulleted list. • In Section 21.2, "PLL Power Supply Filtering," in the second paragraph, changed "provide five independent filter circuits," and "the five AVDD pins" to provide four independent filter circuits," and "the four AVDD pins." • In Table 62, updated note 1 to say the following: "For temperature range = C, processor frequency is limited to 400 with a platform frequency of 266."
6	4/2007	• In Table 3, "Output Drive Capability," changed the values in the Output Impedance column and added USB to the seventh row. • In Section 21.7, "Pull-Up Resistor Requirements,"deleted last two paragraphs and after first paragraph, added a new paragraph. • Deleted Section 21.8, "JTAG Configuration Signals," and Figure 43, "JTAG Interface Connection."
5	3/2007	• Page 1, updated first paragraph to reflect PowerQUICC II Pro information. • In Table 18, "DDR and DDR2 SDRAM Input AC Timing Specifications," added note 2 to t_{CISKEW} and deleted original note 3; renumbered the remaining notes. • In Figure 38, "JTAG Interface Connection," updated with new figure. • In Figure 38, "JTAG Interface Connection," updated with new figure. • In Section 23, "Ordering Information," replaced first paragraph and added a note. • In Section 23.1, "Part Numbers Fully Addressed by this Document," replaced first paragraph.
4	12/2006	Table 19, "DDR and DDR2 SDRAM Output AC Timing Specifications," modified T_{ddkhds} for 333 MHz from 900 ps to 775 ps.